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Vishay/Siliconix SQJ941EP-T1-GE3

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Datasheet of SQJ941EP-T1-GE3 - MOSFET 2P-CH 30V 8A PPAK SO-8

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# Automotive Dual P-Channel 30 V (D-S) 175 °C MOSFET

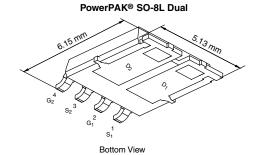
PRODUCT SUMMARY				
V <sub>DS</sub> (V)	- 30			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.024			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.039			
I <sub>D</sub> (A) per leg	- 8			
Configuration	Dual			

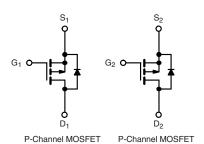
### **FEATURES**

- TrenchFET® Power MOSFET
- 100 % Rq and UIS Tested
- AEC-Q101 Qualified<sup>d</sup>
- Material categorization:
   For definitions of compliance please see www.vishav.com/doc?99912









ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and Halogen-free	SQJ941EP-T1-GE3

ABSOLUTE MAXIMUM RATINGS	<b>S</b> (T <sub>C</sub> = 25 °C, unles	s otherwise noted	l)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		$V_{DS}$	- 30		
Gate-Source Voltage		$V_{GS}$	± 20		
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> = 25 °C	1	- 8		
	T <sub>C</sub> = 125 °C	l <sub>D</sub>	- 8		
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	- 8	Α	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	- 32		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	- 24		
Single Pulse Avalanche Energy	L = 0.1 MH	E <sub>AS</sub>	28.8	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	D	55	W	
	T <sub>C</sub> = 125 °C	$P_{D}$	18.5		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub> - 55 to + 175			
Soldering Recommendations (Peak Temperature)e, f		-	260	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>c</sup>	$R_{thJA}$	85	°C/W	
Junction-to-Case (Drain)		$R_{thJC}$	2.7		

### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.
- e. See solder profile (<a href="www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The PowerPAK SO-8L. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

Document Number: 65546

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static		•						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0, I <sub>D</sub> = - 250 μA		- 30	-		V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$		- 2.0	- 2.5		
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA	
Zero Gate Voltage Drain Current		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 30 V	-	-	- 1		
	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 30 V, T <sub>J</sub> = 125 °C	-	-	- 50	μΑ	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 30 V, T <sub>J</sub> = 175 °C	-	-	- 150		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = - 10 V	V <sub>DS</sub> = - 5 V	- 24	-		Α	
Drain-Source On-State Resistance <sup>a</sup>		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 9 A	-	0.020	0.024	Ω	
		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 9 A, T <sub>J</sub> = 125 °C	-	0.028	0.034		
	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 9 A, T <sub>J</sub> = 175 °C	-	0.032	0.039		
		V <sub>GS</sub> = - 4.5 V	I <sub>D</sub> = - 5 A	-	0.032	0.039		
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 2.5 A		-	10	-	S	
Dynamic <sup>b</sup>		<u> </u>						
Input Capacitance	C <sub>iss</sub>			-	1500	1800		
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{DS} = -10 \text{ V}, f = 1 \text{ MHz}$	-	370	445	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	260	315		
Total Gate Charge <sup>c</sup>	Qg		V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 9 A	-	35	55	nC	
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	V <sub>GS</sub> = - 10 V		-	4.6	-		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>	1		-	8.1			
Gate Resistance	R <sub>g</sub>	f = 1 MHz		2.8	5.95	9.5	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	49	60		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = - 15 V, $R_L$ = 1.66 $\Omega$ $I_D \cong$ - 9 A, $V_{GEN}$ = - 10 V, $R_g$ = 6 $\Omega$		-	35	50	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	47	60		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	26	33		
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	- 32	Α	
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = - 2.5 A, V <sub>GS</sub> = 0		_	- 0.8	- 1.2	V	

#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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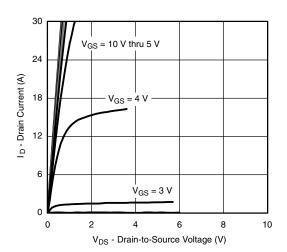


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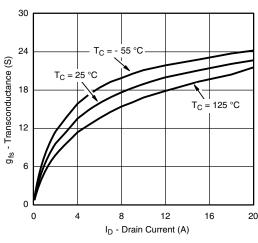


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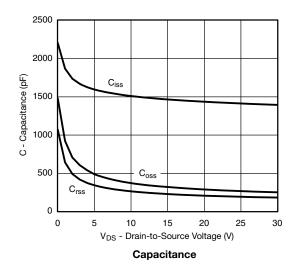
### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)

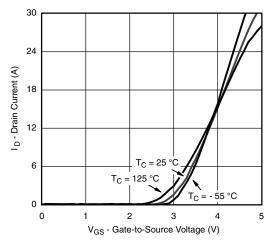


#### **Output Characteristics**

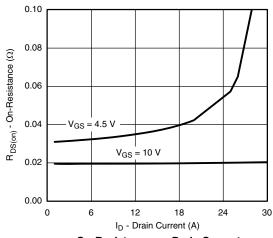


Transconductance

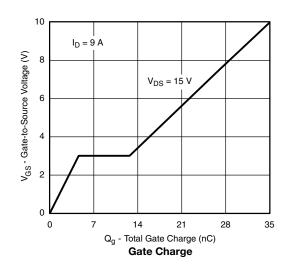




**Transfer Characteristics** 



On-Resistance vs. Drain Current



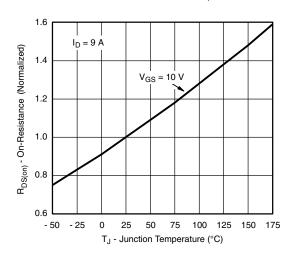




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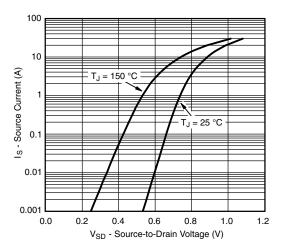
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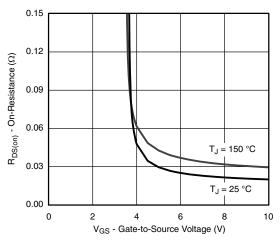


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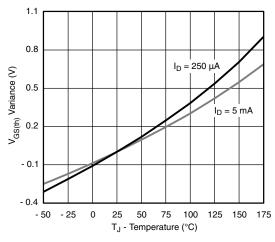
On-Resistance vs. Junction Temperature



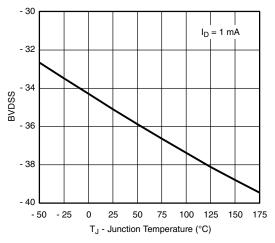
**Source Drain Diode Forward Voltage** 



On-Resistance vs. Gate-to-Source Voltage



**Threshold Voltage** 



**BVDSS vs. Junction Temperature** 

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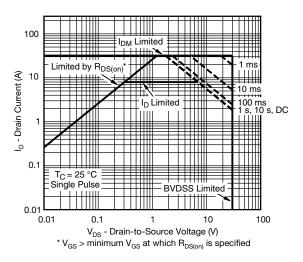
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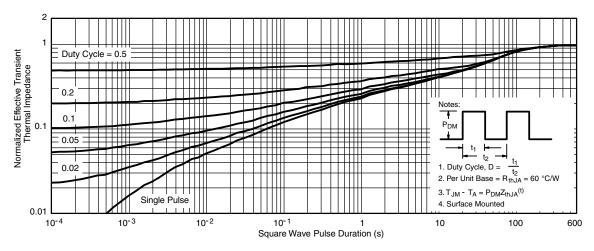


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**THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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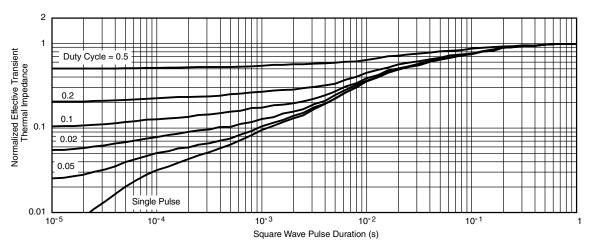


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THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?65546">www.vishay.com/ppg?65546</a>.



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